

TOSHIBA**TC74VHCT367AF/AFN/AFT**

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74VHCT367AF, TC74VHCT367AFN, TC74VHCT367AFT**HEX BUS BUFFER****TC74VHCT367 AF / AFN / AFT NON - INVERTED, 3 - STATE OUTPUTS**

The TC74VHCT367A is advanced high speed CMOS HEX BUS BUFFERs fabricated with silicon gate C²MOS technology.

They achieve the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

They contain six buffers; four buffers are controlled by an enable input ($\bar{G}1$), and the other two buffers are controlled by another enable input ($\bar{G}2$). The outputs of each buffer group are enabled when $\bar{G}1$ and/or $\bar{G}2$ inputs are held low; if held high, these outputs are in a high impedance state.

The TC74VHCT367A is a non-inverting output type.

Input protection and output circuit ensure that 0 to 5.5V can be applied to the input and output*1 pins without regard to the supply voltage. These structure prevents device destruction due to mismatched supply and input/output voltages such as battery back up, hot board insertion, etc.

*1: output in off-state

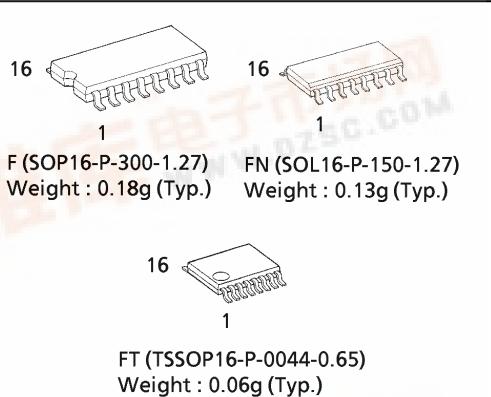
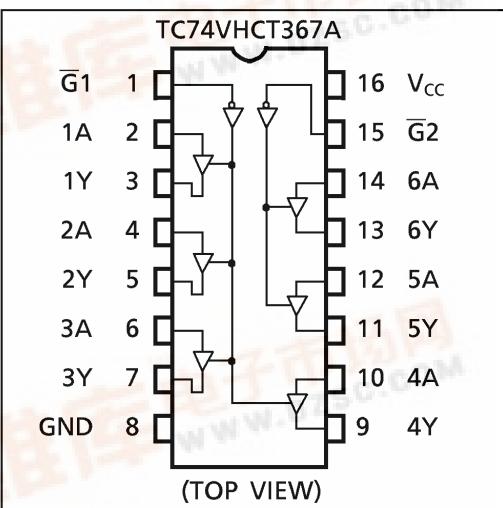
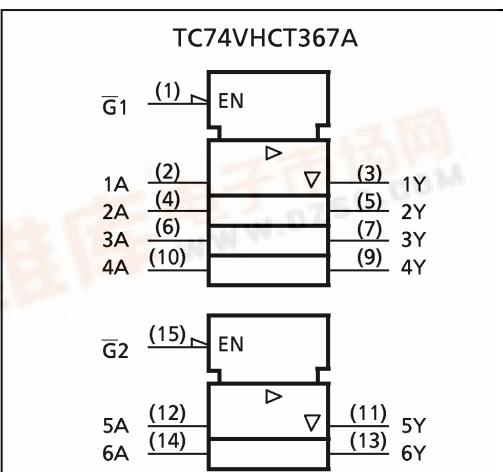
FEATURES:

- High Speed..... $t_{pd} = 5.5\text{ns}$ (typ.) at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}$ (Max.) at $T_a = 25^\circ\text{C}$
- Compatible with TTL outputs ... $V_{IL} = 0.8\text{V}$ (Max.)
 $V_{IH} = 2.0\text{V}$ (Min.)
- Power Down Protection is provided on all inputs and outputs
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Low Noise $V_{OLP} = 0.8\text{V}$ (Max.)
- Pin and Function Compatible with the 74ALS367.

TRUTH TABLE

INPUTS		OUTPUTS
\bar{G}	A	Y
L	L	L
L	H	H
H	X	Z

X : Don't Care
Z : High Impedance

**PIN ASSIGNMENT****IEC LOGIC SYMBOL**

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● TOSHIBA is continually working to improve the quality and the reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to observe standards of safety, and to avoid situations in which a malfunction or failure of a TOSHIBA product could cause loss of human life, bodily injury or damage to property. In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent products specifications. Also, please keep in mind the precautions and conditions set forth in the TOSHIBA Semiconductor Reliability Handbook.

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7.0	V
DC Input Voltage	V_{IN}	-0.5~7.0	V
DC Output Voltage	V_{OUT}	-0.5~7.0 (Note 1)	V
		-0.5~ $V_{CC} + 0.5$ (Note 2)	
Input Diode Current	I_{IK}	-20	mA
Output Diode Current	I_{OK}	± 20 (Note 3)	mA
DC Output Current	I_{OUT}	± 25	mA
DC Vcc/Ground Current	I_{CC}	± 75	mA
Power Dissipation	P_D	180	mW
Storage Temperature	T_{STG}	-65~150	°C

(Note 1) $V_{CC}=0V$ (Note 2) High or Low State. I_{OUT} absolute maximum rating must be observed.(Note 3) $V_{OUT} < GND$, $V_{OUT} > V_{CC}$ **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	4.5~5.5	V
Input Voltage	V_{IN}	0~5.5	V
Output Voltage	V_{OUT}	0~5.5 (Note 4)	V
		0~ V_{CC} (Note 5)	
Operating Temperature	T_{OPR}	-40~85	°C
Input Rise and Fall Time	dt/dV	0~20	ns/V

(Note 4) $V_{CC}=0V$

(Note 5) High or Low State

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DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	CONDITON	V_{CC} (V)	Ta = 25°C			Ta = - 40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		4.5~5.5	2.0	—	—	2.0	—	V
Low - Level Input Voltage	V_{IL}		4.5~5.5	—	—	0.8	—	0.8	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = - 50\mu A$	4.5	4.40	4.50	—	4.40	—
			$I_{OH} = - 8mA$	4.5	3.94	—	—	3.80	—
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 50\mu A$	4.5	—	0.0	0.10	—	0.10
			$I_{OL} = 8mA$	4.5	—	—	0.36	—	0.44
3 - State Output Off - State Current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND	5.5	—	—	± 0.25	—	± 2.50	μA
Input Leakage Current	I_{IN}	$V_{IN} = 5.5V$ or GND	0~5.5	—	—	± 0.1	—	± 1.0	
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	5.5	—	—	4.0	—	40.0	mA
	I_{CCT}	PER INPUT : $V_{IN} = 3.4V$ OTHER INPUT : V_{CC} or GND	5.5	—	—	1.35	—	1.50	
Output Leakage Current	I_{OPD}	$V_{OUT} = 5.5V$	0	—	—	+ 0.5	—	+ 5.0	μA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION		$T_a = 25^\circ\text{C}$			$T_a = -40\sim85^\circ\text{C}$		UNIT
		$V_{CC}(\text{V})$	$C_L(\text{pF})$	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t_{pLH} t_{pHL}	5.0 ± 0.5	15	—	4.7	7.4	1.0	8.5	ns
			50	—	5.2	8.4	1.0	9.5	
3-State Output Enable Time	t_{pZL} t_{pZH}	$R_L = 1\text{k}\Omega$	5.0 ± 0.5	15	—	4.9	10.4	1.0	12.0
				50	—	5.4	11.4	1.0	13.0
3-State Output Disable Time	t_{pLZ} t_{pHZ}	$R_L = 1\text{k}\Omega$	5.0 ± 0.5	50	—	6.3	11.4	1.0	13.0
Output to Output Skew	t_{osLH} t_{osHL}	(Note 6)	5.0 ± 0.5	50	—	—	1.0	—	1.0
Input Capacitance	C_{IN}				—	4	10	—	10
Output Capacitance	C_{OUT}				—	9	—	—	—
Power Dissipation Capacitance (Note 7)	C_{PD}	TC74VHCT367A			—	16	—	—	—

(Note 6) Parameter guaranteed by design. $t_{osLH} = |t_{pLHm} - t_{pLHn}|$, $t_{osHL} = |t_{pHLM} - t_{pHLn}|$ (Note 7) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

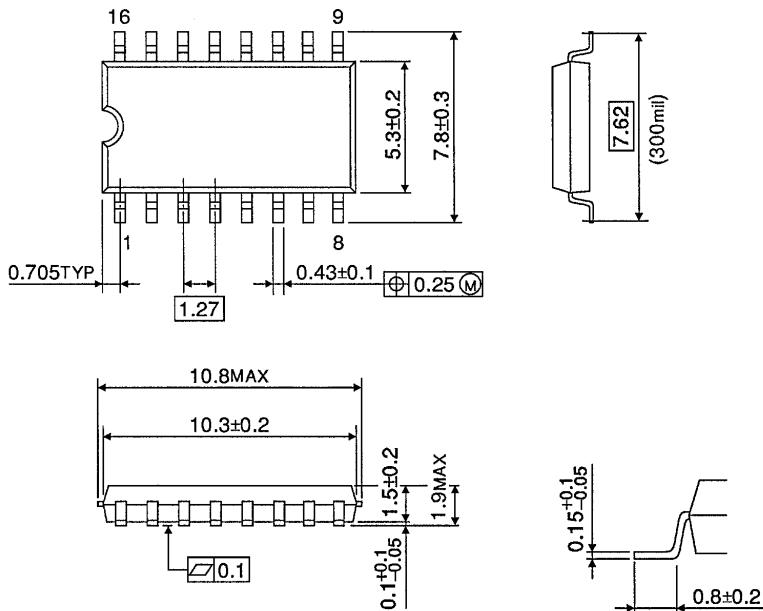
$$I_{CC(\text{opr.})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/6 \text{ (per bit)}$$

NOISE CHARACTERISTICS (Input $t_r = t_f = 3\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION		$T_a = 25^\circ\text{C}$		UNIT
		$V_{CC}(\text{V})$	C_L	TYP.	MAX.	
Quiet Output Maximum Dynamic V_{OL}	V_{OLP}	$C_L = 50\text{pF}$	5.0	0.6	0.8	V
Quiet Output Minimum Dynamic V_{OL}	V_{OLV}	$C_L = 50\text{pF}$	5.0	-0.6	-0.8	V
Minimum High Level Dynamic Input Voltage	V_{IHD}	$C_L = 50\text{pF}$	5.0	—	2.0	V
Maximum Low Level Dynamic Input Voltage	V_{ILD}	$C_L = 50\text{pF}$	5.0	—	0.8	V

SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm

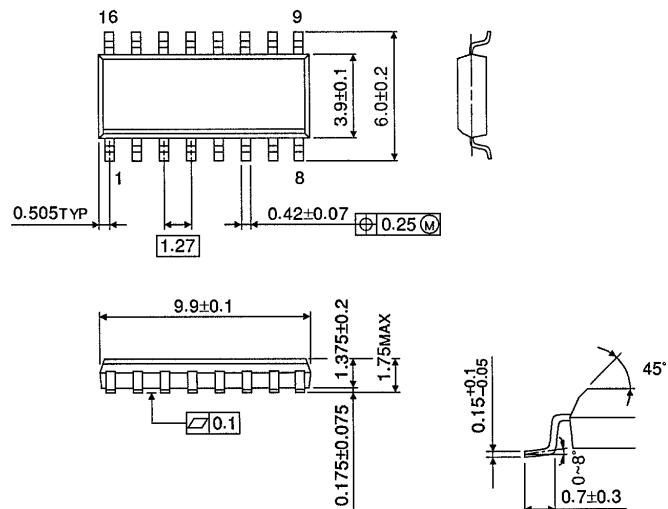


Weight : 0.18g (Typ.)

SOP 16PIN (150mil BODY) OUTLINE DRAWING (SOL16-P-150-1.27)

Unit in mm

(Note) This package is not available in Japan.



Weight : 0.13g (Typ.)

TSSOP 16PIN OUTLINE DRAWING (TSSOP16-P-0044-0.65)

Unit in mm

